

Silicon PNP Power Transistors

2SA807

DESCRIPTION

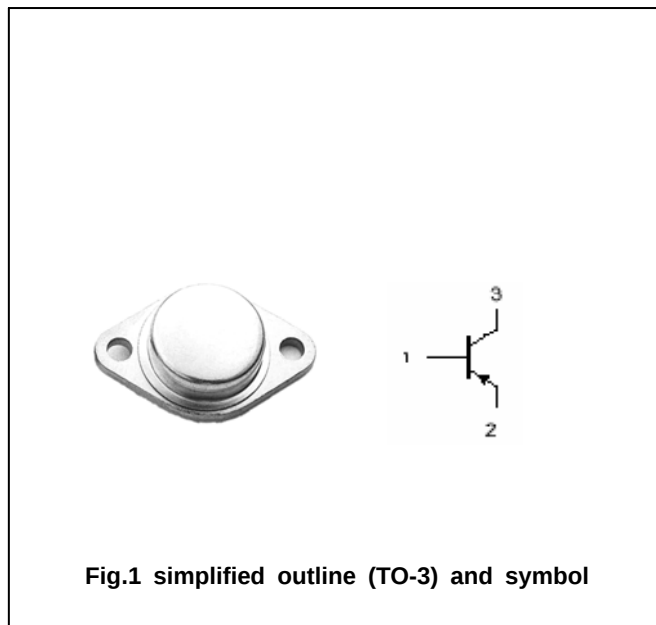
- With TO-3 package
- Wide area of safe operation
- Complement to type 2SC1618

APPLICATIONS

- For power amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_B	Base current		-3	A
P_C	Collector power dissipation	$T_C = 25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA$ $I_B=0$	-60			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A$; $I_B=-0.3A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V$; $I_E=0$			-1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V$; $I_C=0$			-1.0	mA
h_{FE}	DC current gain	$I_C=-3A$; $V_{CE}=-4V$	20			
f_T	Transition frequency	$I_C=-0.5A$; $V_{CE}=-12V$		10		MHz

Switching times

t_r	Rise time	$V_{CC}=-10V$; $I_C=-3A$; $R_L=3\Omega$ $I_{B1}=-0.3A$; $I_{B2}=50mA$		1.2		μs
t_{stg}	Storage time			1.8		μs
t_f	Fall time			0.3		μs

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PACKAGE OUTLINE

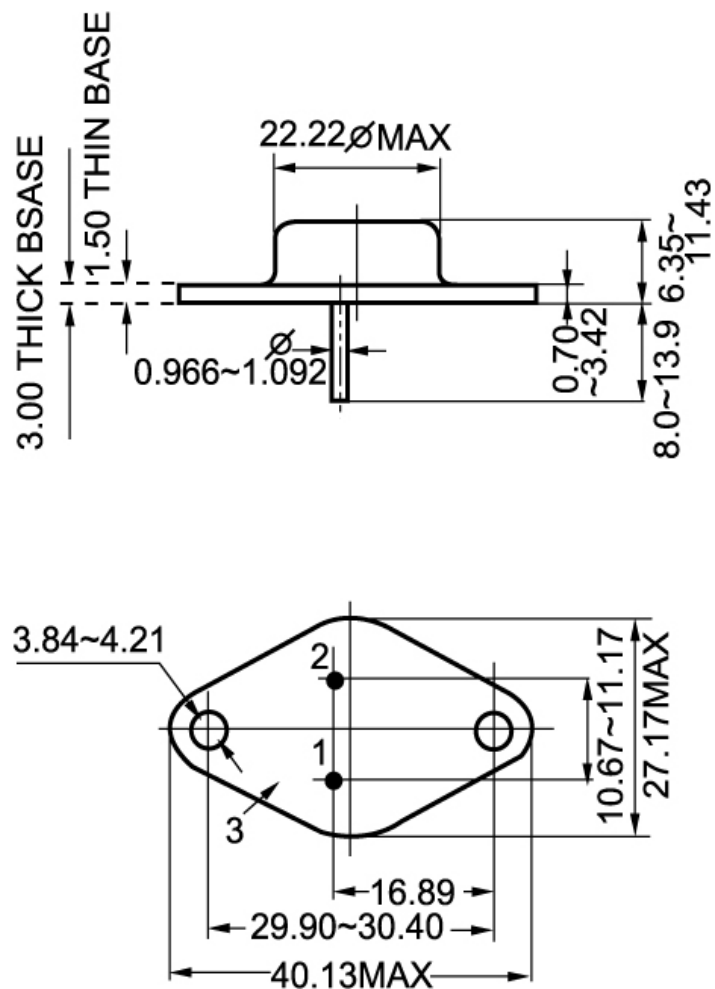


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)